

## Schottky, Silicon Germanium or Recovery (PN) rectifiers?

How to achieve extra efficiency and reliability in LED drivers or solenoid drives by choosing the most suitable power diode

# Introduction

- Dr.-Ing. Reza Behtash
- Application Marketing Manager

## Agenda:

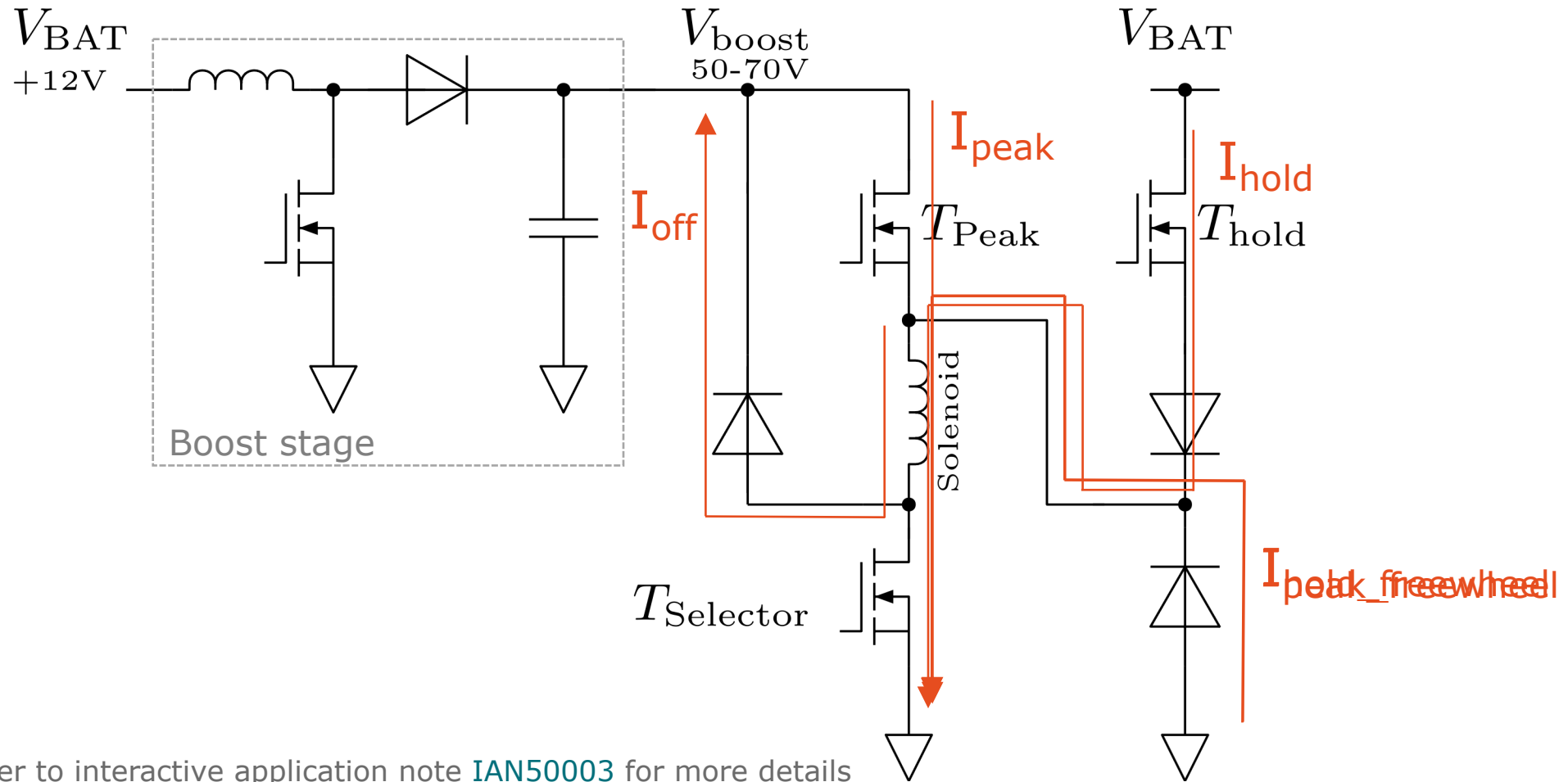
- Diodes in solenoid drivers
- Diodes in LED drivers



# Diodes in solenoid drivers

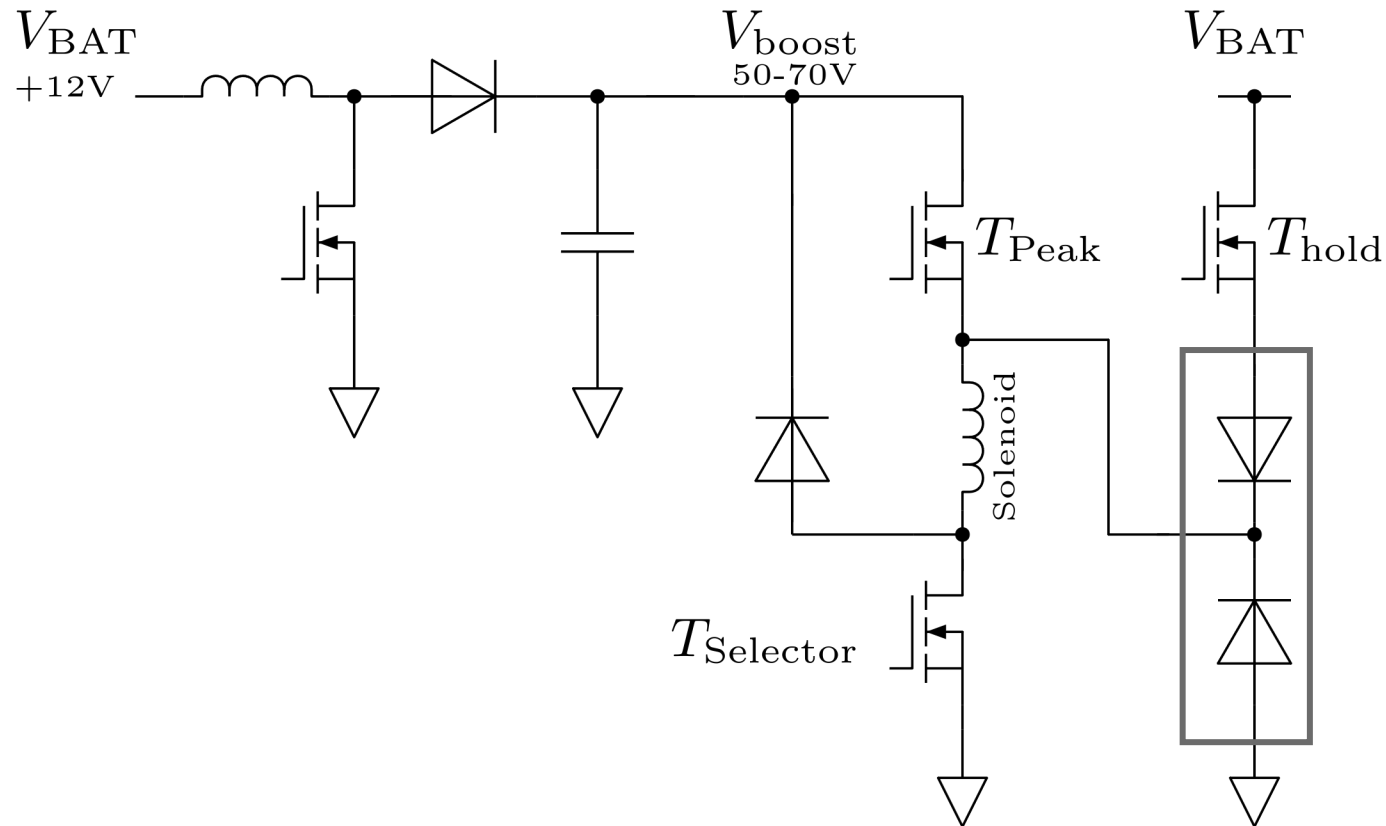
# Solenoid driver

With boost converter in a fuel injection system



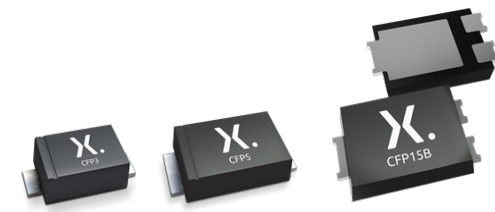
Please refer to interactive application note [IAN50003](#) for more details

# What are the requirements for the diodes?



- Dual die configuration
- Low  $V_f$  for low power dissipation (Peak currents  $\sim$  3-10 A)
- Very low leakage at high ambient temperature ( $\ll$  500  $\mu$ A at 130  $^{\circ}$ C)
- At least 100 V blocking voltage
- Switching losses not dominating
- High IFSM robustness
- Wide SOA
- High reliability

# Recovery Rectifiers | Product Portfolio

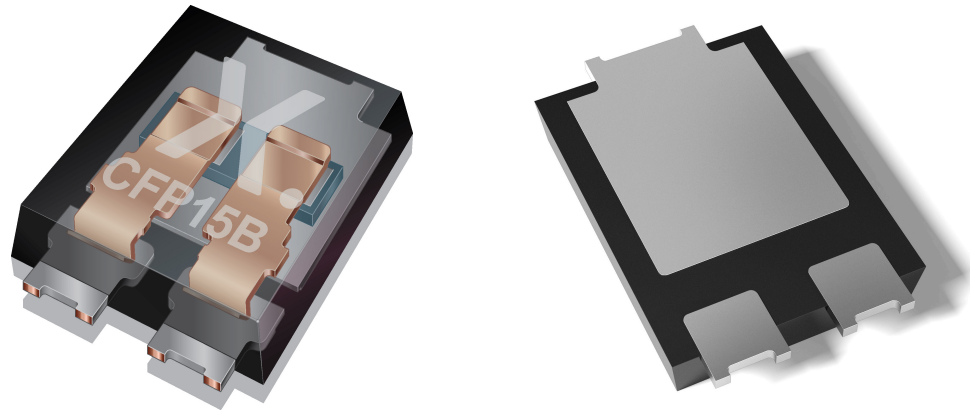


Nexperia's has a complete 200V portfolio and building the 650V portfolio

Type	Package	$V_R$ max [V]	$I_{f(AV)}$ max [A]	$V_f$ max @ $I_{F(AV)}$ [mV]	$I_R$ max [ $\mu$ A]	$t_{rr}$ typ [ns]	Configuration	$T_j$ (max) [ $^{\circ}$ C]	AEC-Q101
PNE20010ER	CFP3	200	1	930	0.2	10	single	175	✓
PNE20020ER	CFP3	200	2	980	0.2	10	single	175	✓
PNE20020EP	CFP5	200	2	950	1	10	single	175	✓
PNE20030EP	CFP5	200	3	980	1	13	single	175	✓
PNE20040CPE	CFP15B	200	2 x 2	960	1	13	dual, cc	175	✓
PNE20060CPE	CFP15B	200	2 x 3	940	1	13	dual, cc	175	✓
PNE20080CPE	CFP15B	200	2 x 4	930	1	12	dual, cc	175	✓
PNE200100CPE	CFP15B	200	2 x 5	950	1	12	dual, cc	175	✓
PNU650V10ER	CFP3	650	1	1250	5	35	single	175	✓
PNU650V10EP	CFP5	650	1	1250	5	35	Single	175	✓

# Recovery Rectifiers in CFP15B package

Highly reliable clip bonded Flatpower package CFP15B



- Solid copper clip:
  - low parasitic inductance
  - high surge robustness (IFSM)
- Exposed heat sink for best thermal performance
- Single and dual die configuration
- 60% space saving on PCB compared to DPAK
- Tin-plated lead ends optimized for AOI

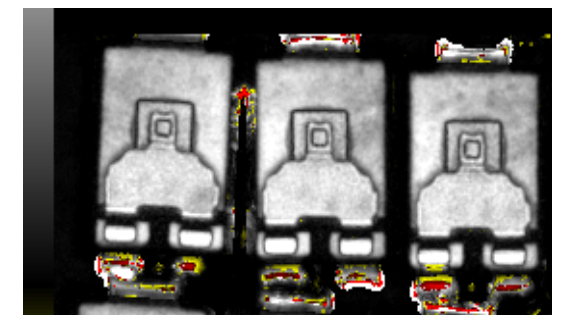
## Reliability beyond AEC-Q101

- Extended reliability testing – 2 times AEC-Q101 qualified
- Zero delamination
- Board level reliability tested:
  - bending test
  - vibration test
  - power temperature cycling
  - drop test

12mm bending



Zero delam after MSL

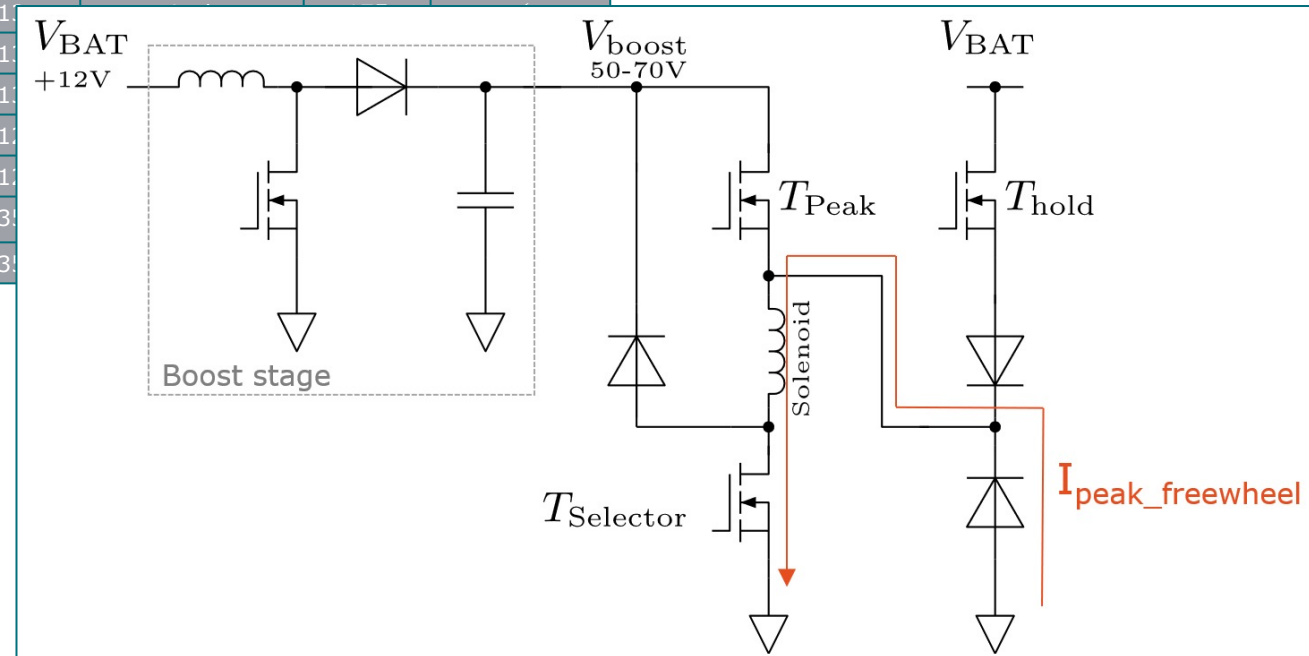


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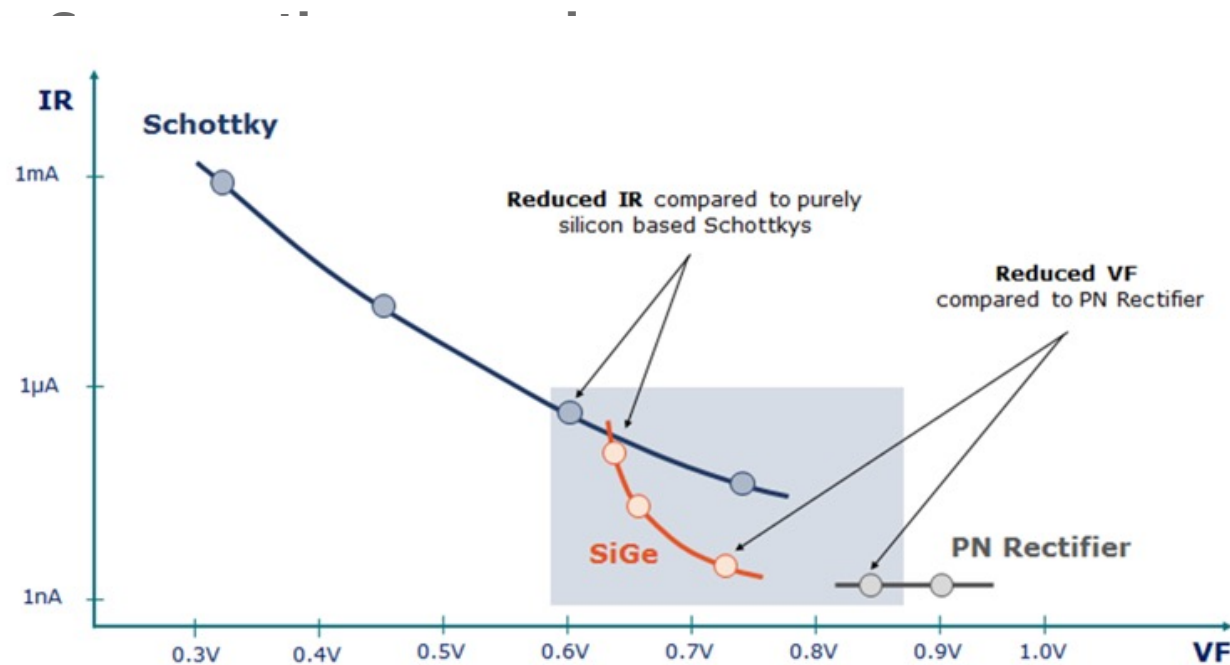
How to improve  $V_f$  without sacrificing advantages of recovery rectifiers (low leakage, thermal stability)?



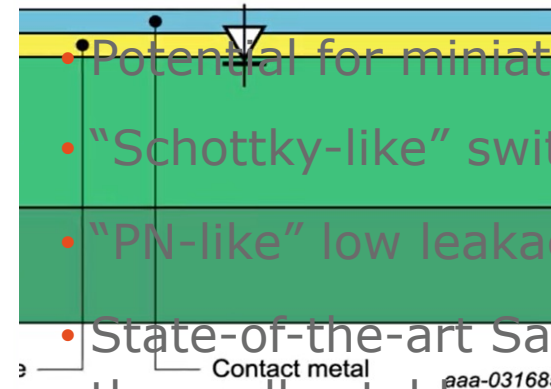


# SiGe Rectifiers | An Innovative Technology

Silicon germanium (SiGe) – a technology with unique value propositions



- Excellent  $I_r/V_f$  trade-off – reducing conduction losses



- Potential for miniaturization
- “Schottky-like” switching
- “PN-like” low leakage current
- State-of-the-art Safe Operation Area – thermally stable up to almost  $T_A = 175^\circ\text{C}$
- 2x AEC-Q101 qualified portfolio

# SOA – SiGe technology

Life comparison to same class Schottky rectifier



## Experiment set up:

- Schottky and SiGe diode (120 V) in reverse bias
- Chuck temperature is increased, and the leakage currents are monitored

## Result:

- SiGe diode offering an extremely wide SOA
- SiGe diodes leakage current orders of magnitude less than Schottky counterpart

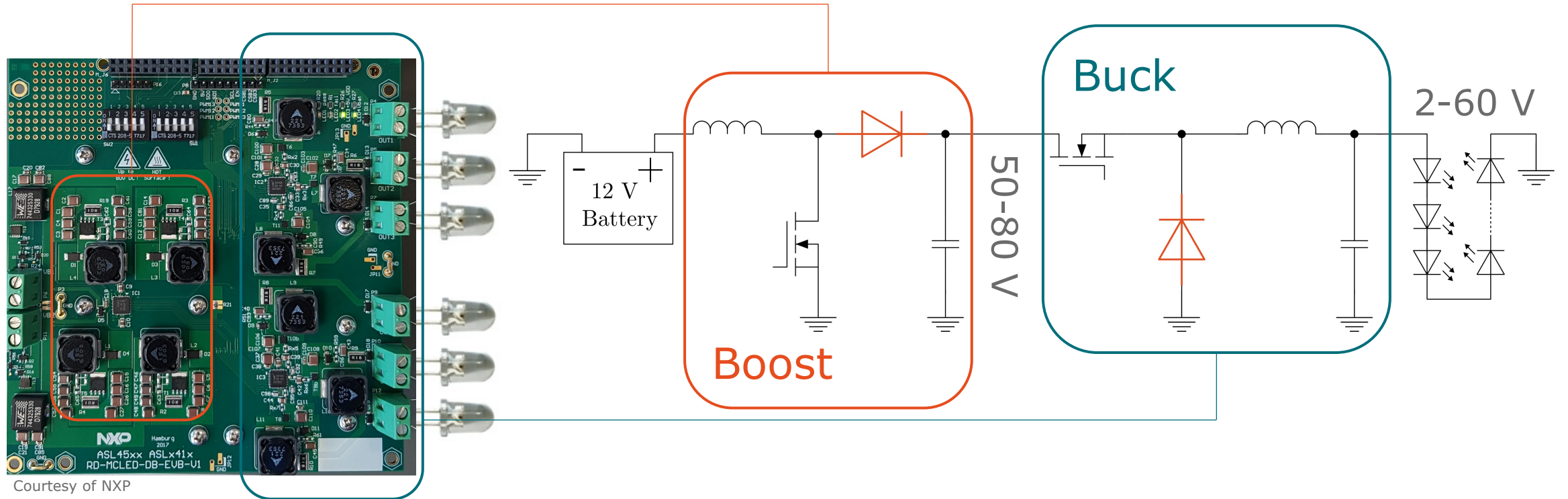


# Diodes in LED drivers

Asynchronous LED drivers

# Switched-mode converter

For instance, asynchronous boost / buck stage of a LED driver



# Switched-mode converter

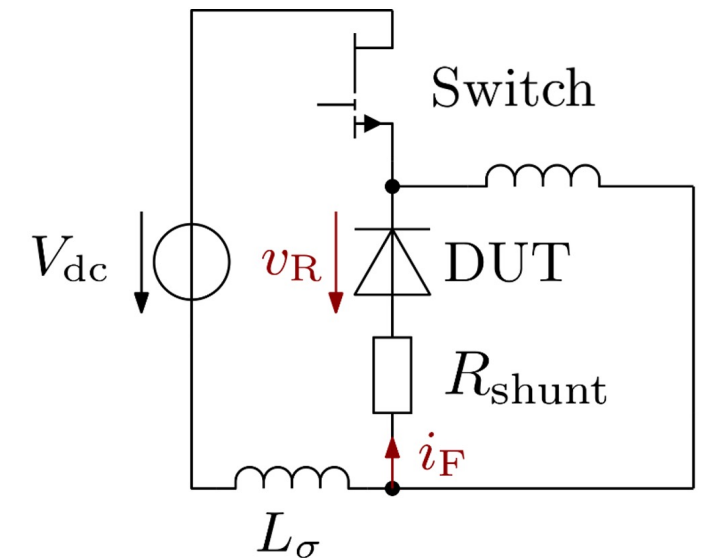
Requirements concerning the rectifiers in the boost and buck stage

- **Low reverse recovery charge  $Q_{rr}$** : for every switching cycle the reverse recovery charge  $Q_{rr}$  is dissipated in the MOSFET, a major contribution to the switching losses of the converter
- **High thermal stability**: in high power density applications, rectifiers with a broad Safe operating area (SOA) are needed. Thermal runaway of the rectifier must not happen
- **Low electromagnetic emission**: the rectifier is supposed to have minimal impact on the conducted and radiated electromagnetic emission levels of the converter
- **Low forward voltage-drop**: voltage forward drop of the rectifier impacting the conduction losses – though not dominating the overall efficiency

# Double pulse test circuit

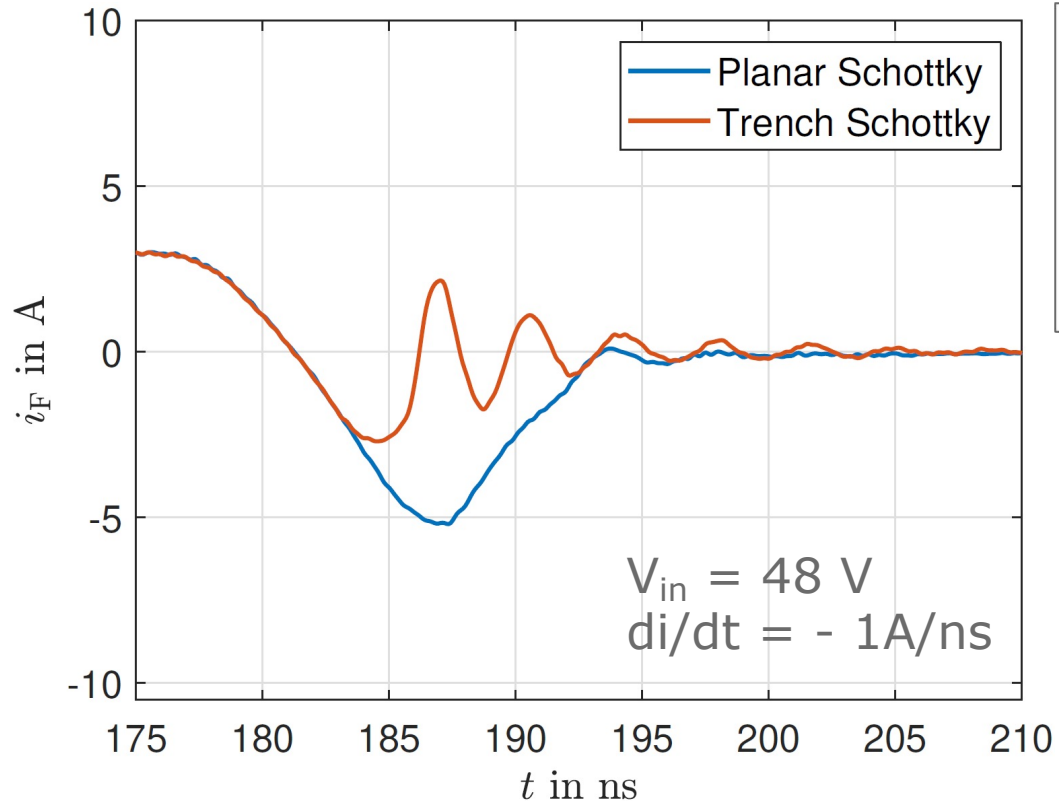
Standard method for measuring the switching performance

- Collaboration with Helmut-Schmidt-University in Hamburg
- A double pulse test characterizes all switching phases of the DUT:
  - First pulse characterizes the turn-on behavior
  - Second pulse characterizes the turn-off behavior
- High  $di/dt$  ( $-1A/ns$ ) –  $V_{DC}=48 V$
- DUT at defined temperature
- Optimized design to keep  $L_s$  minimal ( $\sim 5 nH$ )



# Superior switching performance with Trench Schottky

Double pulse measurements at  $T_{amb} = 85^\circ$



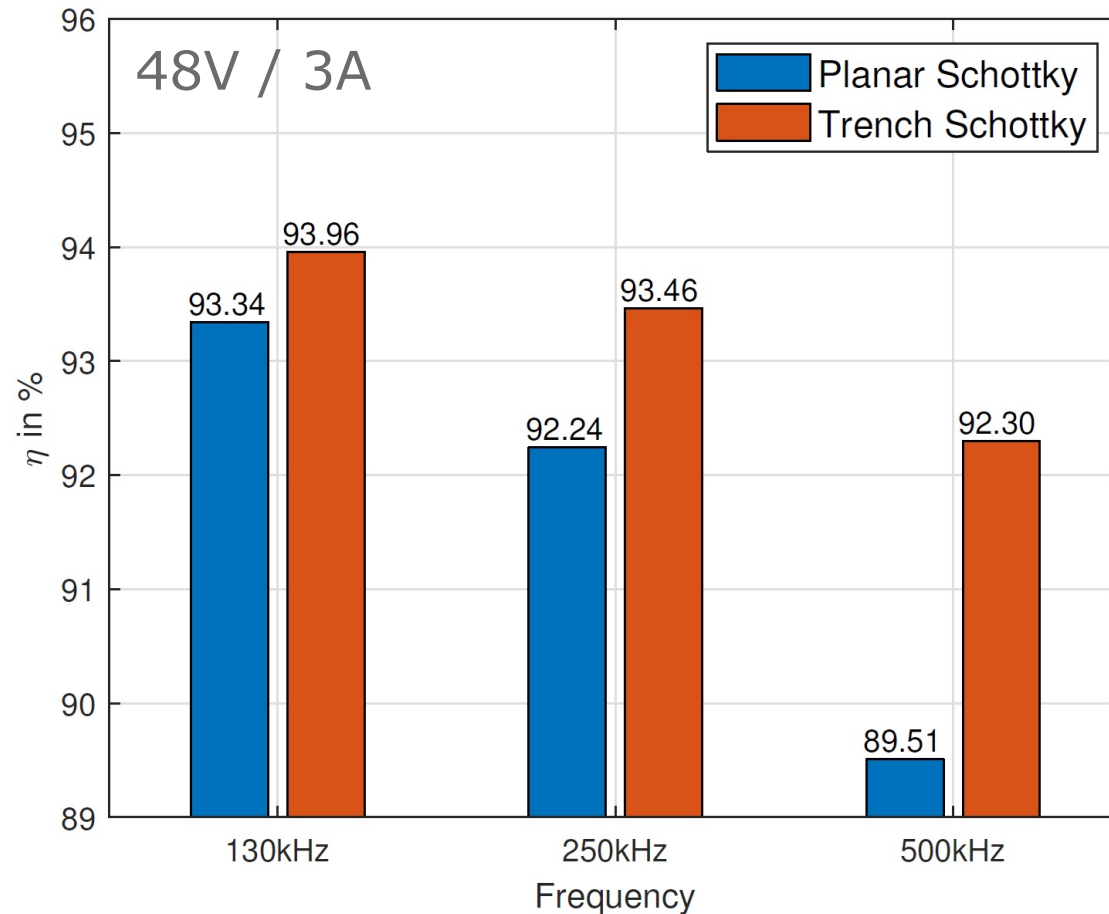
	$Q_{rr}^{T_c=25^\circ\text{C}}$ [nC]	$Q_{rr}^{T_c=85^\circ\text{C}}$ [nC]	$I_{rrm}^{T_c=25^\circ\text{C}}$ [A]	$I_{rrm}^{T_c=85^\circ\text{C}}$ [A]
Trench Schottky	8.6	8.5	2.8	2.7
SiGe	19.1	25.5	4.4	4.9
Recovery A	37.3	52.1	7.1	8.1
Planar Schottky	26.3	33.5	5.2	5.2
Recovery B	33.5	44.4	8.2	8.9

Trench Schottky Vs. planar Schottky:

- Less stored charge  $Q_{rr}$  of Trench rectifier compared to planar Schottky rectifier
- No increase of  $Q_{rr}$  of Trench rectifier over temperature ( $25\text{ }^\circ\text{C} \rightarrow 85\text{ }^\circ\text{C}$ )

# Low $Q_{rr}$ – high converter efficiency with Trench

48 V-12 V buck converter as test vehicle – 3 A rectifiers in SOD128



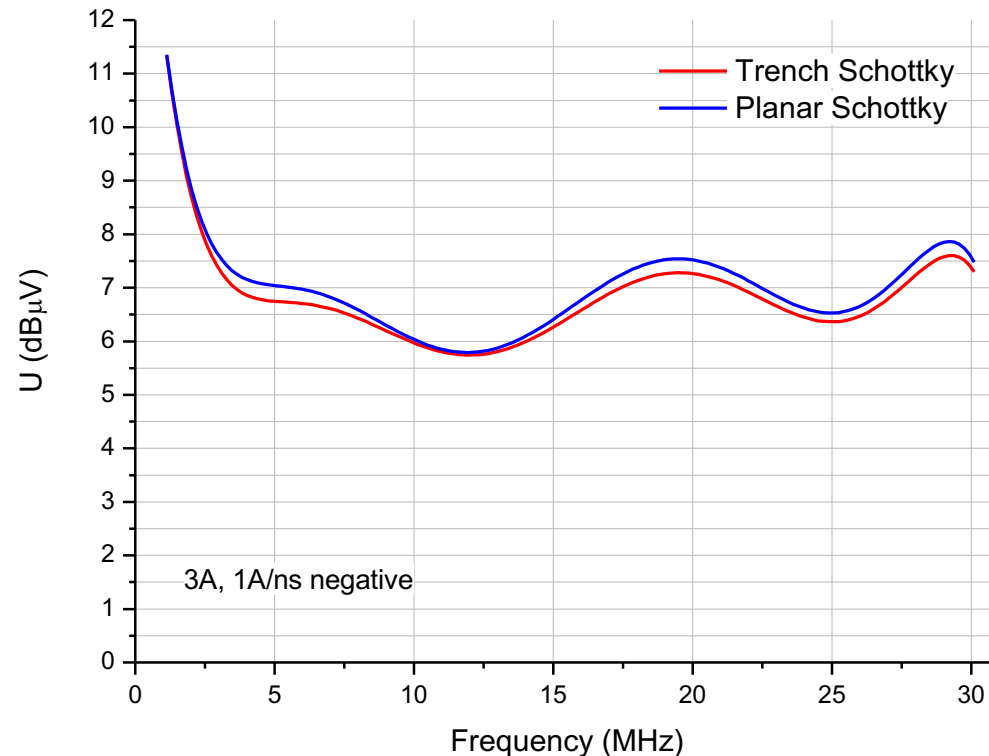
- Higher converter efficiency achieved with Trench rectifier compared to planar Schottky
- The higher the frequency, the higher switching losses, the bigger the Trench advantage



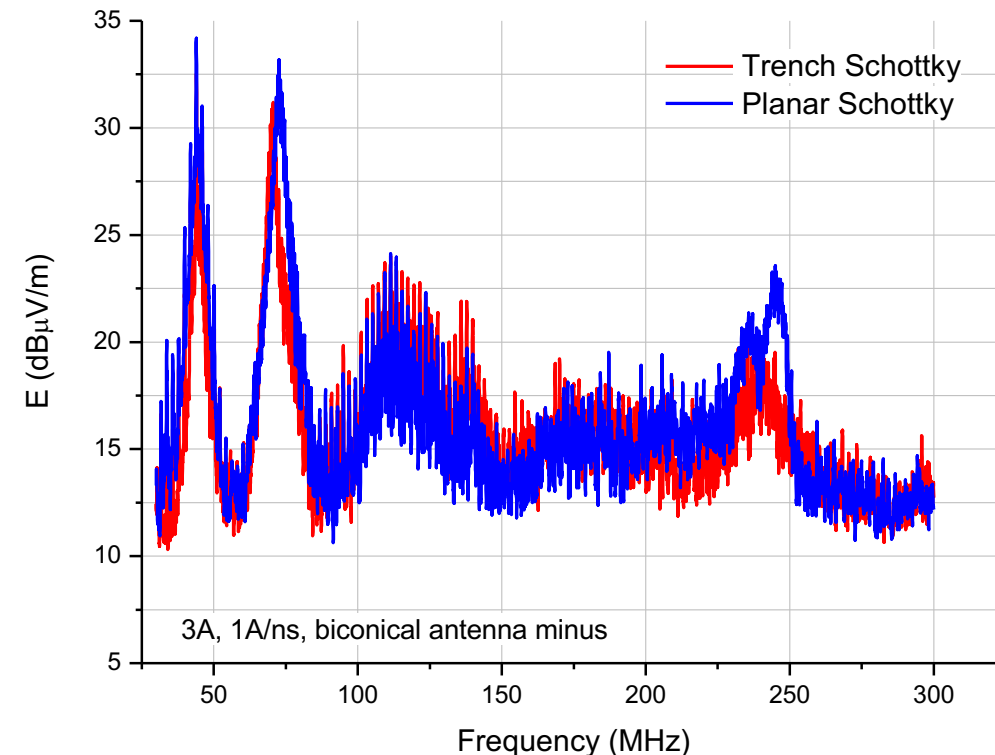
# Impact on electromagnetic emission

48 V-12 V buck converter as test vehicle – 3 A rectifiers in SOD128

## Conducted emission



## Radiated emission



**No increased electromagnetic emission levels despite observed ringing of Trench rectifier during switching**

# Conclusion

- Solenoid driver:
  - Go with 200V hyper fast recovery rectifier
  - Use dual die configuration in CFP15B package for state-of-the-art reliability
  - If you want to optimize further by reducing  $V_f$ , take a look at the SiGe technology
- LED driver:
  - The best choice for highest efficiency is the Trench Schottky
  - Keep in mind Nexperia Trench Schottkys products deliver extra efficiency and thermal safety margin

# How to receive more information

- Interactive application note on driving solenoids: Search IAN50003 on [www.nexperia.com](http://www.nexperia.com)
- Find the suitable Trench Schottky rectifier: [www.nexperia.com/trench-schottky-rectifiers](http://www.nexperia.com/trench-schottky-rectifiers)
- Find out more about SiGe rectifiers: [www.nexperia.com/sige-rectifiers](http://www.nexperia.com/sige-rectifiers)
- Visit our *efficiencywins* blogs: <https://efficiencywins.nexperia.com/> (filter: diodes)
- Contact us directly
- Sample boxes can be ordered from Power Live page

Please share your  
questions and insights

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